

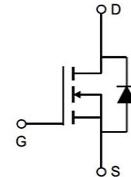
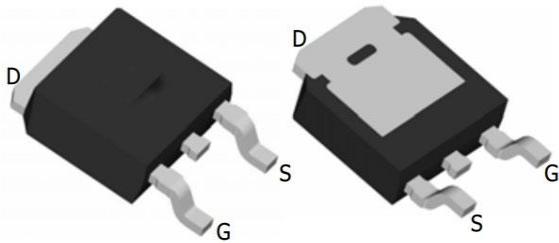
30V /55A Single N Power MOSFET
General Description

30V /55A Single N Power MOSFET

Very low on-resistance RDS(on) @ VGS=4.5 V

Pb-free lead plating; RoHS compliant

V_{DS}	30	V
R_{DS(on),TYP@VGS=10V}	3.9	mΩ
R_{DS(on),TYP@VGS=4.5}	6.7	mΩ
I_D	55	A



Part ID	Package Type	Marking	Tape and reel infomation
SM4146T9RL	TO-252	55N03	2500


 100% UIS Tested
100% RG Tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	20	±V
Continuous Drain Current A	I _D	55.0	A
		43*	
Pulsed Drain Current B	I _{DM}	88.0	
Avalanche Current G	I _{AR}	17.6	
Repetitive avalanche energy L=0.1mH G	E _{AR}	40.5	mJ
Power Dissipation A	P _D	62	W
		31*	
Junction and Storage Temperature Range	T _J , T _{TSG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	R _{θJA}	23	35	°C/W
Maximum Junction-to-Ambient A		47	57	°C/W
Maximum Junction-to-Lead c	R _{θJL}	14	22	°C/W

STATIC PARAMETERS

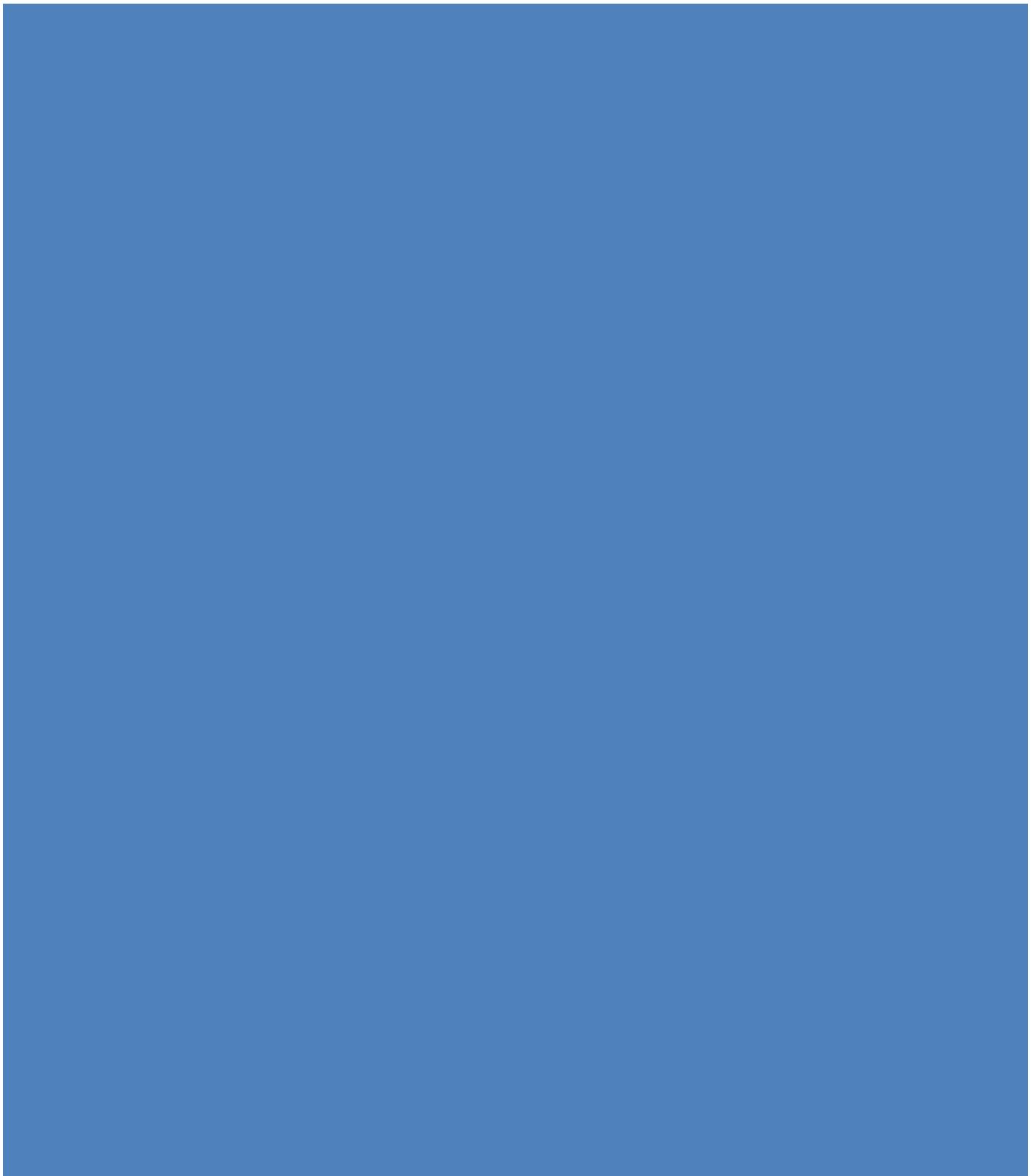
Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu A, V_{GS} = 0V$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	uA
					5	
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.5	2.3	3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		3.9	5.6	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$		6.7	9.5	
g_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=20A$		67		S
V_{SD}	Diode Forward Voltage	$I_S=1A, V_{GS}=182V$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				55	A

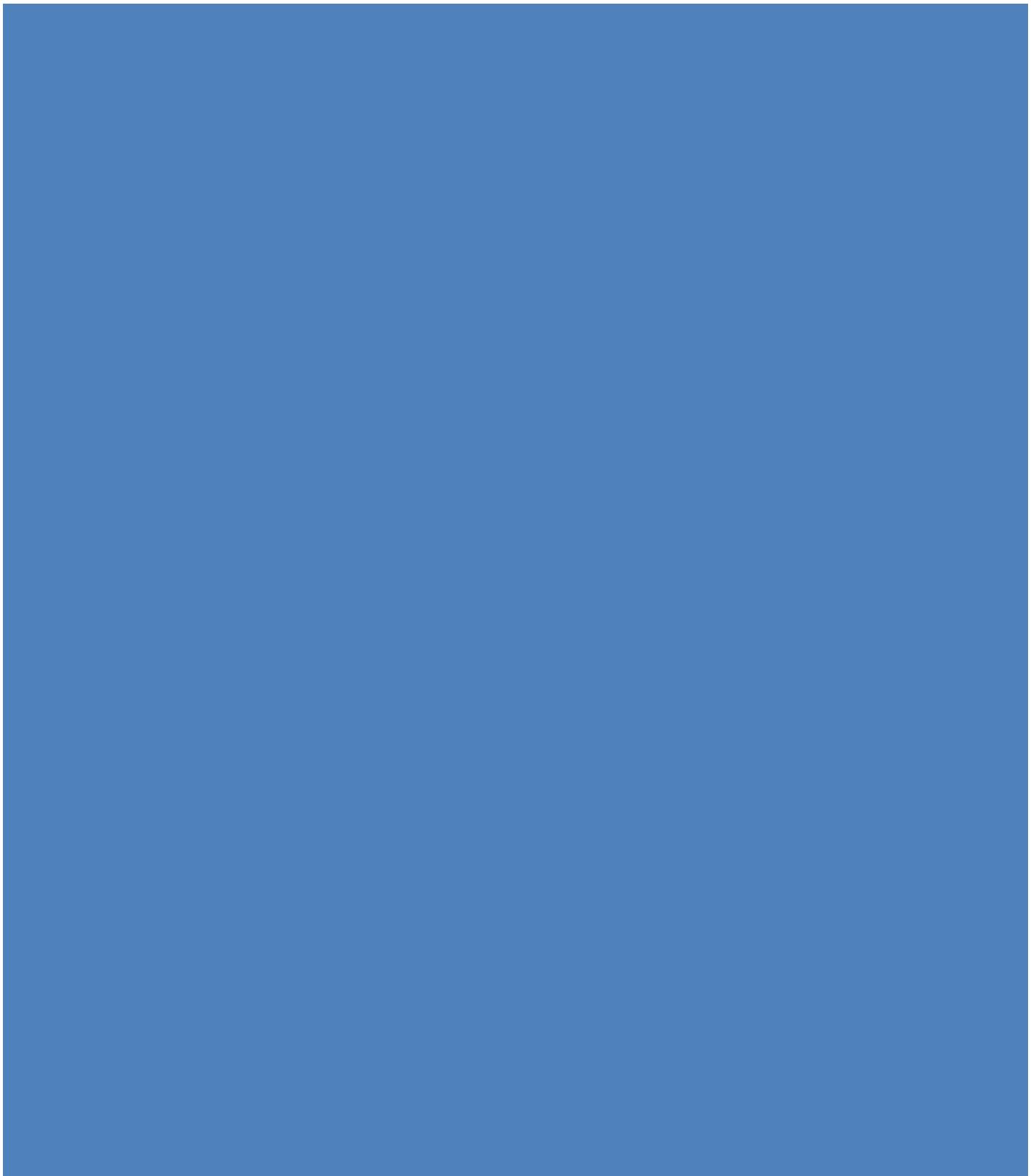
DYNAMIC PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=15V, f=1MHz$		2037	2485	pF
C_{oss}	Output Capacitance			375	461	pF
C_{rss}	Reverse Transfer Capacitance			220	261	pF
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$			2.3	Ω

SWITCHING PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$Q_g(10V)$	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		16		nC
$Q_g 4.5V$	Total Gate Charge			8		
Q_{gs}	Gate Source Charge			3.22		
Q_{gd}	Gate Drain Charge			4.6		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10V, V_{DS}=15V, RL=0.75\Omega, R_{GEN}=3\Omega$		5		ns
t_r	Turn-On Rise Time			4		
$t_{D(off)}$	Turn-Off Delay Time			14		
t_f	Turn-Off Fall Time			4.5		
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-8A, dI/dt=500A/\mu s$		10		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=18A, dI/dt=500A/\mu s$		15		nC





X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by SPS manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#)
[424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#)
[IPS70R2K0CEAKMA1](#) [RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#)
[NTE6400](#) [JANTX2N6796U](#) [JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#)